#4 IDS

Sheet 1 of 1

Form PTO-1449 (REV. 8-83) US Dept. of Commerce PATENT & TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY DOCKET NO. 111779	APPLICATION NO. New U.S. Patent Application
	APPLICANTS Akihiko EBINA, Yutaka MARUO	
	FILING DATE January 23, 2002	

J1046 U.S. PTO
10/052549
01/23/02

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	1	~~New U.S. Patent Application (Atty. docket # 111778)~~	~~01/23/2002~~	~~Ebina et al.~~		
MDP	2	6,255,166 B1	07/03/2001	Ogura et al.		
MDP	3	5,408,115	04/18/1995	Chang		
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	9	~~JP B1 2978477 (w/English translation)~~	~~09/10/1999~~	~~Japan~~		
MDP	10	JP A 7-161851 (w/English translation)	06/23/1995	Japan		
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

MDP	12	Hayashi et al., "Twin MONOS Cell with Dual Control Gates", IEEE VLSI Technology Digest, 2000.
MDP	13	Chang et al. "A New SONOS Memory Using Source-Side Injection for Programming", IEEE ELECTRON DEVICE LETTERS, Vol. 19, No. 7, July 1998, pp. 253-255.
MDP	14	Chen et al., "A Novel Flash Memory Device with S PIit Gate Source Side Injection and ONO Charge Storage Stack (SPIN), VLSI Technology Digest, pp. 63-64, 1997.

EXAMINER	DATE CONSIDERED 11/23/2002

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.